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Hex Schmitt-trigger Inverters



ADE-205-064B(Z)

Rev.2 September 1995

Description

The HD74LVC14 has six schmitt trigger inverters in a 14 pin package. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

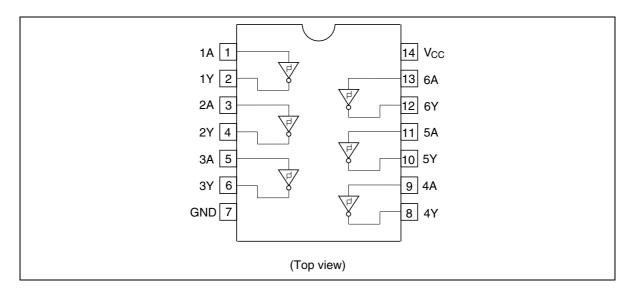
- $V_{CC} = 2.0 \text{ V to } 5.5 \text{ V}$
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{CC} = 3.0 V to 5.5 V)

Function Table

Input A	Output Y
L	Н
Н	L

H: High level L: Low level

Pin Arrangement



Absolute Maximum Ratings

Item	n Symbol Ratings		Unit	Conditions		
Supply voltage range	V _{cc}	-0.5 to 6.0	V			
Input diode current	I _{IK}	-50	mA	V ₁ = -0.5 V		
Input voltage	V,	-0.5 to 6.0	V			
Output diode current	I _{OK}	-50	mA	V ₀ = -0.5 V		
		50	mA	$V_{o} = V_{cc} + 0.5 \text{ V}$		
Output voltage	V _o	-0.5 to V _{cc} +0.5	V			
Output current	I _o	±50	mA			
V _{cc} , GND current / pin	I _{CC} or I _{GND}	100	mA			
Storage temperature	Tstg	-65 to +150	°C			

Note: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	1.5 to 5.5	V	Data retention
		2.0 to 5.5	V	At operation
Input / Output voltage	V,	0 to 5.5	V	A
	V_{\circ}	0 to V _{cc}	V	Υ
Operating temperature	Ta	-40 to 85	°C	
Output current	I _{OH}	-12	mA	V _{cc} = 2.7 V
		-24 ^{*2}	mA	$V_{cc} = 3.0 \text{ V to } 5.5 \text{ V}$
	I _{OL}	12	mA	V _{cc} = 2.7 V
		24 ^{*2}	mA	V _{cc} = 3.0 V to 5.5 V
Input rise / fall time ^{*1}	t _r , t _f	10	ns/V	

Notes: 1. This item guarantees maximum limit when one input switches.

Waveform: Refer to test circuit of switching characteristics.

2. duty cycle $\leq 50\%$

Electrical Characteristics

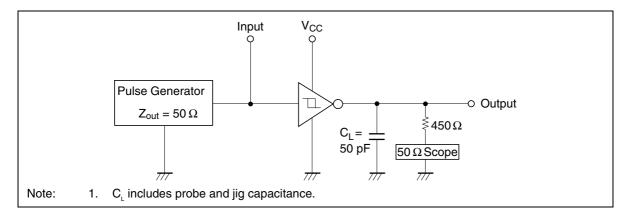
	Ta = -40 to 85°C					
Item	Symbol	V _{cc} (V)	Min	Max	Unit	Test Conditions
Threshould voltage	V _T +	2.7	1.0	2.0	V	
		3.0	1.2	2.2	٧	_
		3.6	1.5	2.4	٧	_
		4.5	1.6	2.6	V	-
		5.5	2.0	3.0	V	_
	V	2.7	0.4	1.4	٧	_
		3.0	0.6	1.5	٧	_
		3.6	0.8	1.8	٧	_
		4.5	1.0	2.0	٧	_
		5.5	1.4	2.4	٧	_
Hysteresis voltage	V _H	2.7	0.3	1.1	٧	$V_T^+ - V_T^-$
		3.0	0.4	1.2	٧	_
		3.6	0.4	1.2	٧	_
		4.5	0.4	1.2	٧	_
		5.5	0.4	1.2	٧	_
Input voltage	V _{IH}	2.7 to 3.6	2.4	_	V	
		4.5 to 5.5	3.0	_	٧	_
	V _{IL}	2.7 to 3.6	_	0.4	٧	_
		4.5 to 5.5	_	1.0	٧	_
Output voltage	V _{OH}	2.7 to 5.5	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.7	2.2	_	V	$I_{OH} = -12 \text{ mA}$
		3.0	2.4	_	V	$I_{OH} = -12 \text{ mA}$
		3.0	2.0	_	V	I _{OH} = -24 mA
		4.5	3.8	_	V	I _{OH} = -24 mA
	V _{oL}	2.7 to 5.5	_	0.2	٧	I _{OL} = 100 μA
		2.7	_	0.4	V	I _{OL} = 12 mA
		3.0	_	0.55	V	I _{oL} = 24 mA
		4.5	_	0.55	V	I _{oL} = 24 mA
Input current	I _{IN}	0 to 5.5	_	±5.0	μΑ	V _{IN} = 5.5 V or GND
Quiescent supply current	I _{cc}	5.5	_	20	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	500	μΑ	V_{IN} = one input at $(V_{CC}-0.6)V$, other inputs at V_{CC} or GND

Switching Characteristics

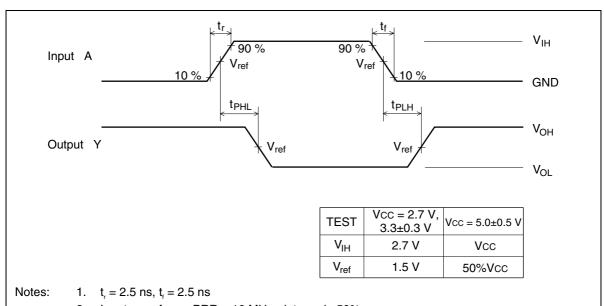
Ta = -40 to 85° C

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	From (Input)	To (Output)
Propagation delay time	t _{PLH}	2.7	_	6.0	9.5	ns	Α	Υ
	$t_{_{PHL}}$	3.3±0.3	1.5	5.0	8.5	ns	_	
		5.0±0.5	_	3.5	7.0	ns	_	
Input capacitance	C _{IN}	2.7	_	3.0	_	рF		
Output capacitance	C _o	2.7	_	15.0	_	pF		

Test Circuit

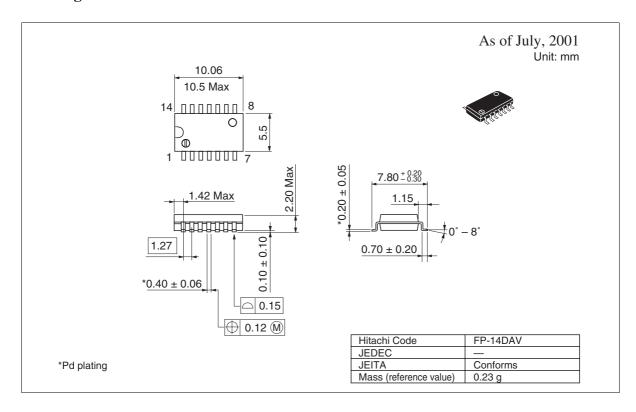


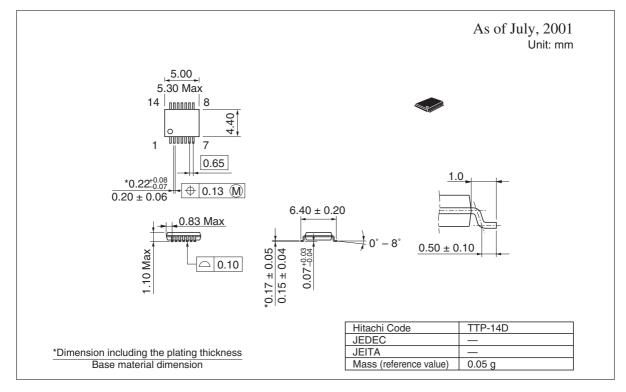
Waveforms



2. Input waveform : PRR = 10 MHz, duty cycle 50%.

Package Dimensions





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